

Vishay Siliconix

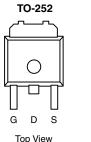
P-Channel 60 V (D-S), 175 °C MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A)		
- 60	0.015 at V _{GS} = - 10 V	- 50 ^d		
- 60	0.020 at V _{GS} = - 4.5 V	- 50		

FEATURES

- TrenchFET[®] Power MOSFET
- 175 °C Junction Temperature
- Compliant to RoHS Directive 2002/95/EC





Drain Connected to Tab

Top View

Ordering Information: SUD50P06-15L-E3 (Lead-(Pb)-free)

G 0−−− 1 − 4	
ç	2
L	J

s Î

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A	= 25 °C, unless other	rwise noted)			
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	- 60	v	
Gate-Source Voltage		V _{GS}	± 20	v	
Continuous Drain Current ($T_1 = 175 \text{ °C}$)	T _C = 25 °C	1-	- 50 ^d	A	
	T _C = 125 °C	I _D	- 39		
Pulsed Drain Current		I _{DM}	- 80		
Avalanche Current		I _{AR}	- 50		
Repetitive Avalanche Energy ^a	L = 0.1 mH	E _{AR}	125	mJ	
Power Dissinction	T _C = 25 °C	P _D	136 ^c	w	
Power Dissipation	T _A = 25 °C		3 ^{b, c}		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
lunction to Archient	t ≤ 10 s	- R _{thJA}	15	18	°C/W
Junction-to-Ambient ^o	Steady State		40	50	
Junction-to-Case		R _{thJC}	0.82	1.1	

Notes:

a. Duty cycle \leq 1 %.

b. When mounted on 1" square PCB (FR-4 material).

c. See SOA curve for voltage derating.

d. Package limited.

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Parameter	Symbol	Test Conditions	Test Conditions Min. Typ.		Max.	Unit
Static	•	·		•		
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, \text{ I}_{D} = -250 \mu\text{A}$ - 60			V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = -250 \ \mu A$	- 1		- 3	V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA
	I _{DSS}	$V_{DS} = -48 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			- 1	
Zero Gate Voltage Drain Current		$V_{DS} = -48 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125 \text{ °C}$			- 50	μA
		$V_{DS} = -48 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 175 ^{\circ}\text{C}$	V _{GS} = 0 V, T _J = 175 °C		- 150	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = -5 V, V_{GS} = -10 V$	- 50			А
		V _{GS} = - 10 V, I _D = - 17 A		0.012	2 0.015	
	D	V_{GS} = - 10 V, I _D = - 50 A, T _J = 125 °C			0.025	0
Drain-Source On-State Resistance ^a	R _{DS(on)}	V_{GS} = - 10 V, I _D = - 50 A, T _J = 175 °C	0.03		0.030	Ω
		V _{GS} = - 4.5 V, I _D = - 14 A			0.020	1
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 17 A		61		S
Dynamic ^b		· · · · ·				
Input Capacitance	C _{iss}			4950		pF
Output Capacitance	C _{oss}	$V_{GS} = 0 V$, $V_{DS} = -25 V$, f = 1 MHz		480		
Reverse Transfer Capacitance	C _{rss}			405		
Total Gate Charge ^c	Qg			110	165	
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = -30 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -50 \text{ A}$		19		nC
Gate-Drain Charge ^c	Q _{gd}]		28		
Turn-On Delay Time ^c	t _{d(on)}			15	23	
Rise Time ^c	t _r	V_{DD} = - 30 V, R_L = 0.6 Ω		70	105	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D\cong$ - 50 A, V_{GEN} = - 10 V, R_G = 6 Ω		175	260	- ns
Fall Time ^c	t _f] [175	260	
Source-Drain Diode Ratings and Cha	racteristics	(T _C = 25 °C) ^b				
Continuous Current	۱ _S				- 50	٨
Pulsed Current	I _{SM}				- 80	A
Forward Voltage ^a	V _{SD}	I _F = - 50 A, V _{GS} = 0 V		1.0	1.6	V
Reverse Recovery Time	t _{rr}	I _F = - 50 A, dI/dt = 100 A/μs	45 70		ns	

Notes:

a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

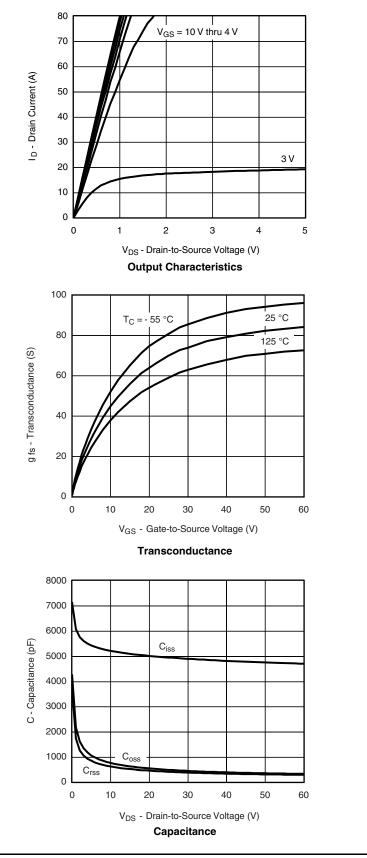
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

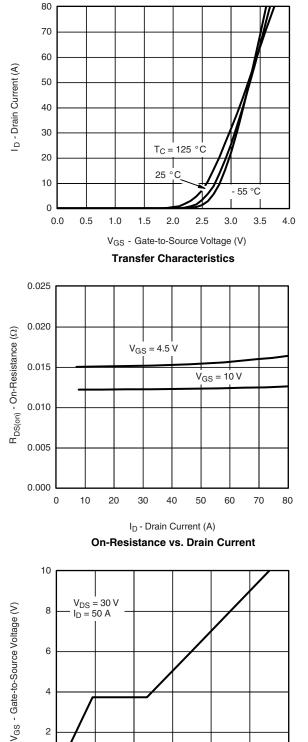


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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





4

2

0

0

20

40

60

Qg - Total Gate Charge (nC)

Gate Charge

80

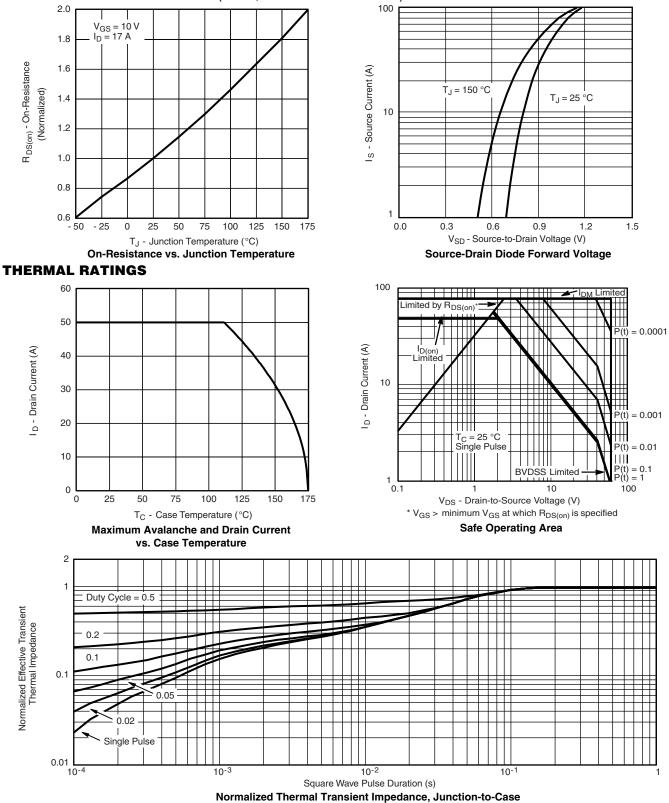
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?72250.





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